

## **Electronic Supplementary Information (ESI)**

# **New Insight into High-Temperature Driven Morphology Reliant CoMoO<sub>4</sub> Flexible Supercapacitor**

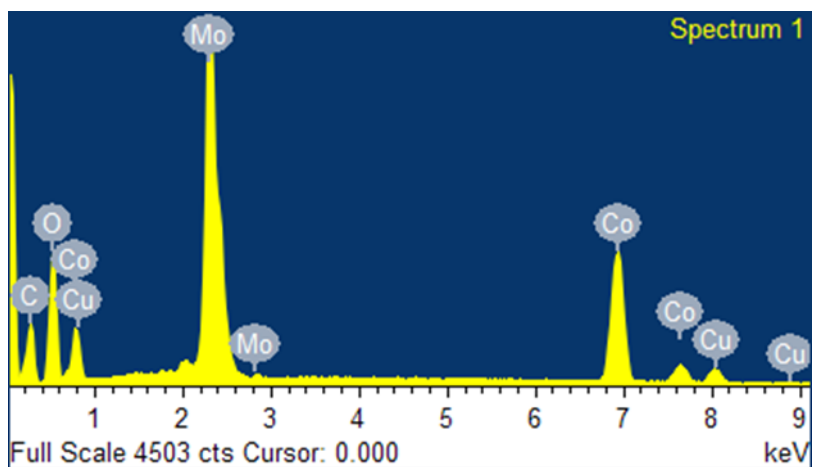
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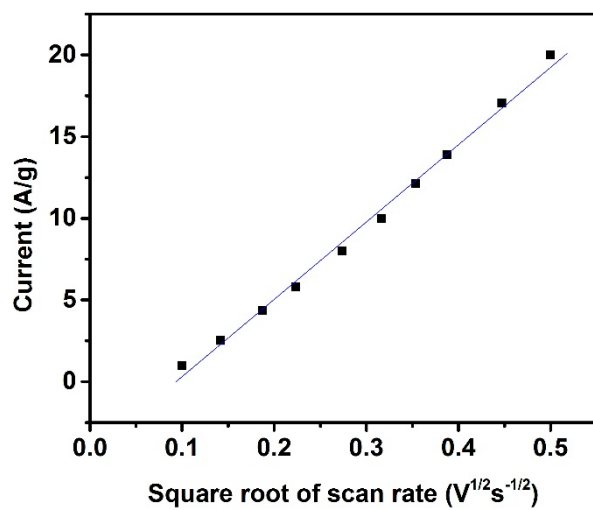
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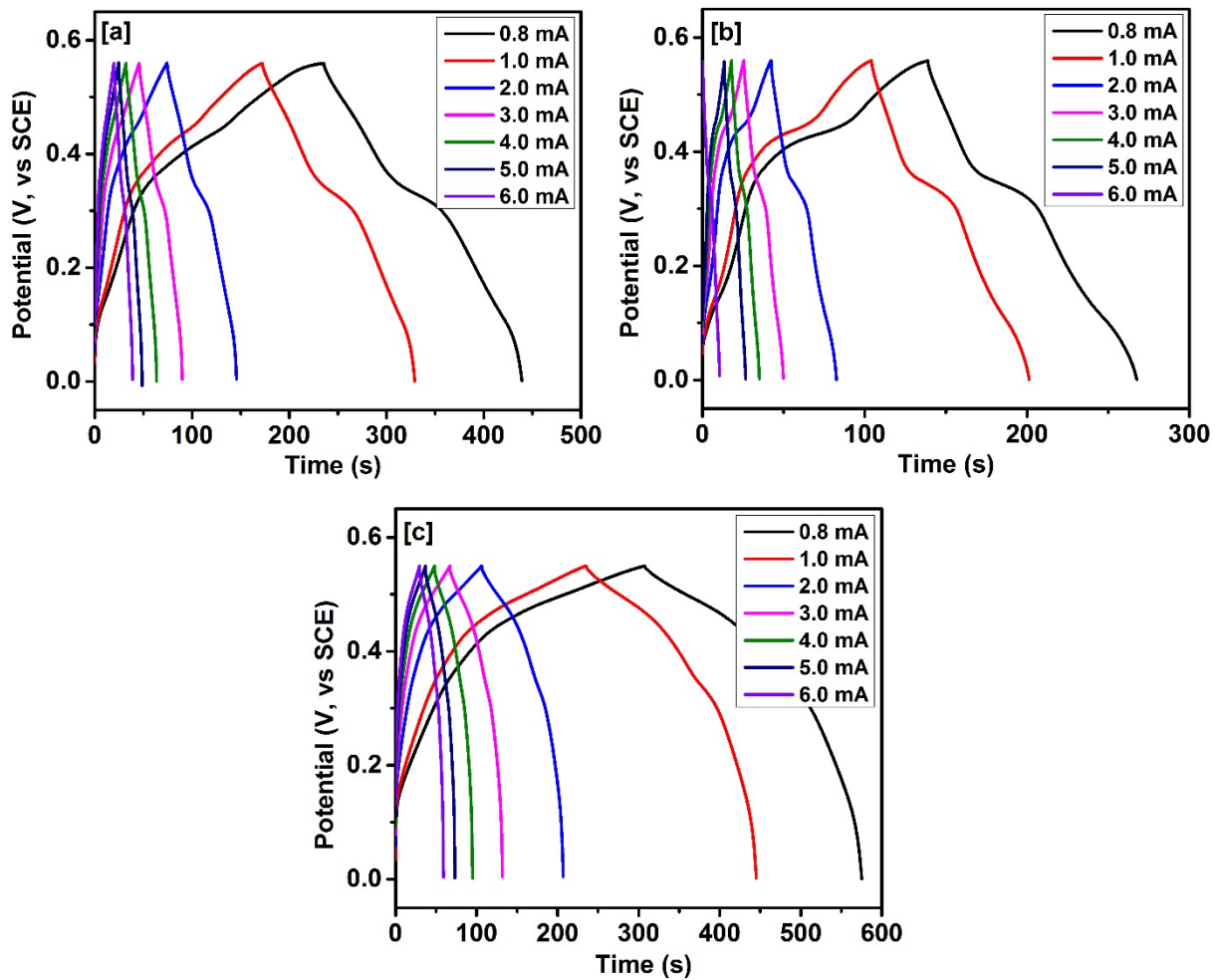
<sup>d</sup>Center for Materials for Information Technology, The University of Alabama, Tuscaloosa, AL-  
35487



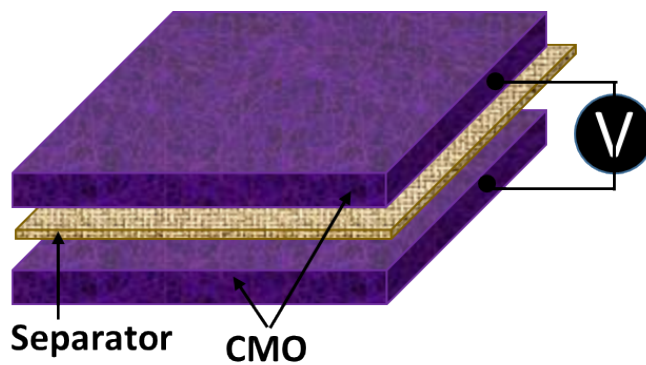
**Fig. 1S:** Energy-dispersive X-ray spectroscopy of CMO-3.



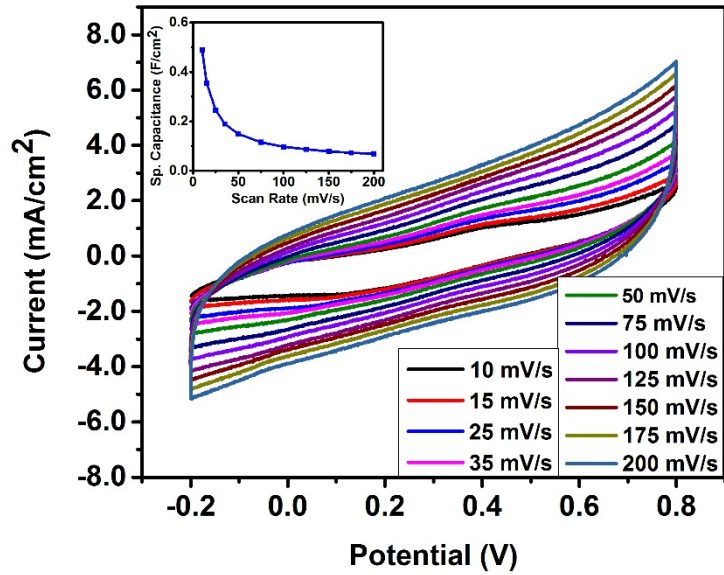
**Fig. 2S:** Variation of peak current as a function of square root of scan rate for CMO-3.



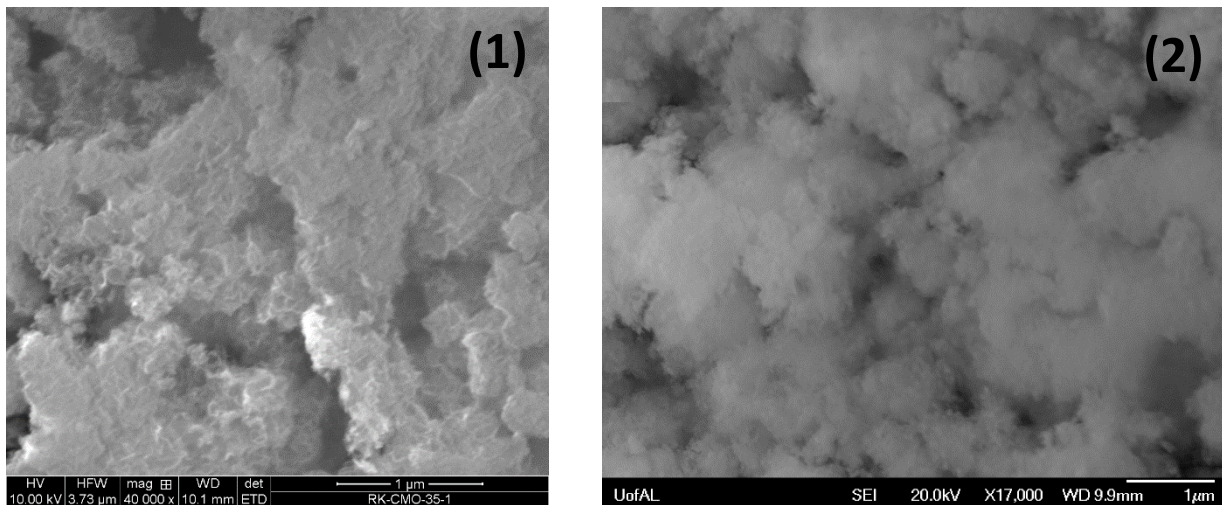
**Fig. 3S:** Galvanostatic charge-discharge characteristics of (a) CMO-1, (b) CMO-2, and (c) CMO-3 at different currents in 3M KOH electrolyte.



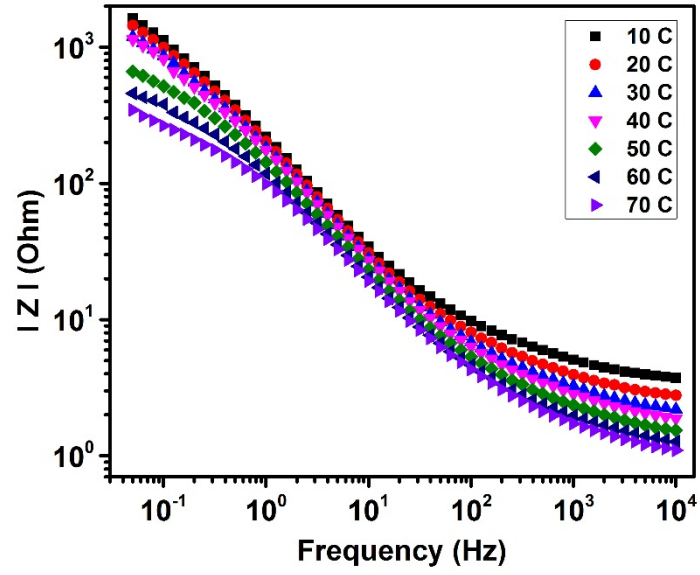
**Fig. 4S:** Schematic diagram of the fabricated device.



**Fig. 5S:** CV curves of the device at various scan rates. Inset figure shows the specific capacitance vs scan rate for the same device.



**Fig. 6S:** SEM images of CMO-3 before (1) and after (2) bending and electrochemical measurements at high temperature.



**Fig. 7S:** Z vs frequency plots of the device at various temperatures.